

MMBT6517L, NSVMMBT6517L

High Voltage Transistor

NPN Silicon

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	350	V
Collector – Base Voltage	V_{CBO}	350	V
Emitter – Base Voltage	V_{EBO}	5.0	V
Base Current	I_B	25	mA
Collector Current – Continuous	I_C	100	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

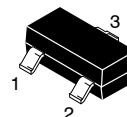
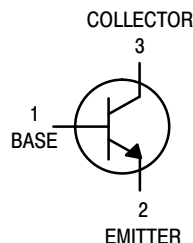
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



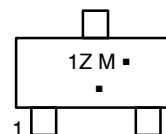
ON Semiconductor®

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SOT-23 (TO-236AB)
CASE 318
STYLE 6

MARKING DIAGRAM



1Z = Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT6517LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT6517LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
NSVMMBT6517LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I _C = 1.0 mA)	V _{(BR)CEO}	350	–	V
Collector–Base Breakdown Voltage (I _C = 100 µA)	V _{(BR)CBO}	350	–	V
Emitter–Base Breakdown Voltage (I _E = 10 µA)	V _{(BR)EBO}	6.0	–	V
Collector Cutoff Current (V _{CB} = 250 V)	I _{CBO}	–	50	nA
Emitter Cutoff Current (V _{EB} = 5.0 V)	I _{EBO}	–	50	nA

ON CHARACTERISTICS

DC Current Gain (I _C = 1.0 mA, V _{CE} = 10 V) (I _C = 10 mA, V _{CE} = 10 V) (I _C = 30 mA, V _{CE} = 10 V) (I _C = 50 mA, V _{CE} = 10 V) (I _C = 100 mA, V _{CE} = 10 V)	h _{FE}	20 30 30 20 15	– – 200 200 –	–
Collector–Emitter Saturation Voltage (Note 3) (I _C = 10 mA, I _B = 1.0 mA) (I _C = 20 mA, I _B = 2.0 mA) (I _C = 30 mA, I _B = 3.0 mA) (I _C = 50 mA, I _B = 5.0 mA)	V _{CE(sat)}	– – – –	0.30 0.35 0.50 1.0	V
Base–Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA) (I _C = 20 mA, I _B = 2.0 mA) (I _C = 30 mA, I _B = 3.0 mA)	V _{BE(sat)}	– – –	0.75 0.85 0.90	V
Base–Emitter On Voltage (I _C = 100 mA, V _{CE} = 10 V)	V _{BE(on)}	–	2.0	V

SMALL–SIGNAL CHARACTERISTICS

Current Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 20 V, f = 20 MHz)	f _T	40	200	MHz
Collector–Base Capacitance (V _{CB} = 20 V, f = 1.0 MHz)	C _{cb}	–	6.0	pF
Emitter–Base Capacitance (V _{EB} = 0.5 V, f = 1.0 MHz)	C _{eb}	–	80	pF

3. Pulse Test: Pulse Width = 300 µs, Duty Cycle = 2.0%.

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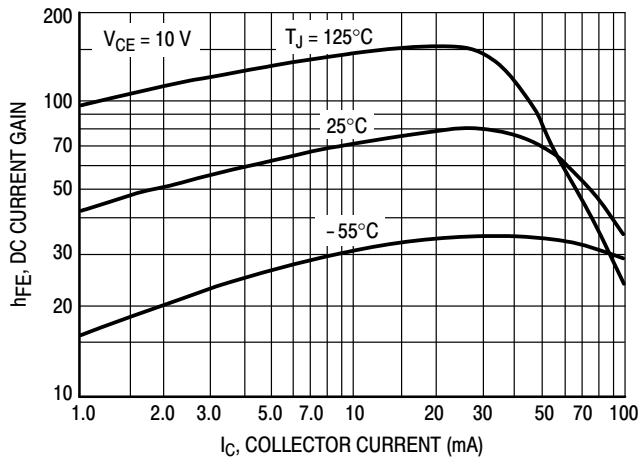


Figure 1. DC Current Gain

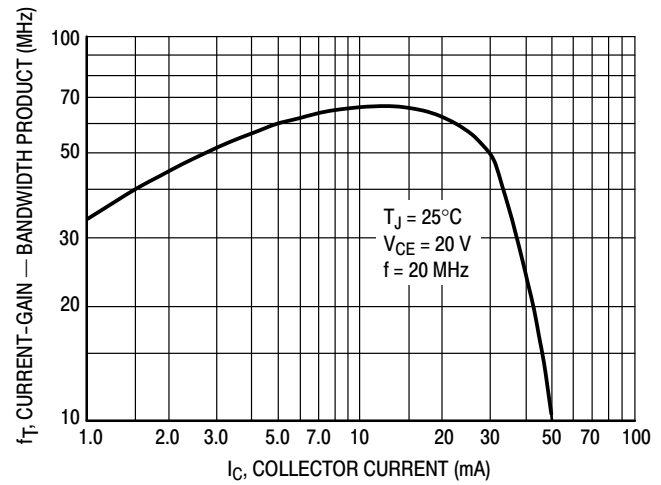


Figure 2. Current-Gain — Bandwidth Product

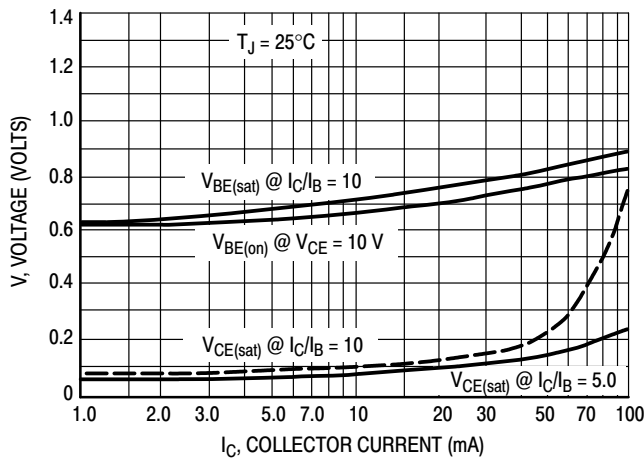


Figure 3. "On" Voltages

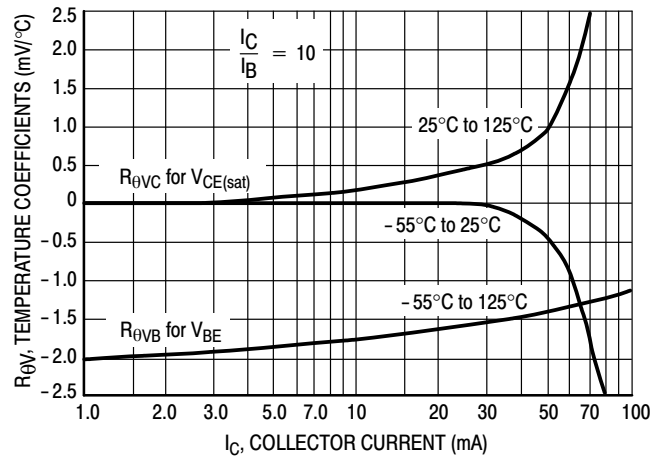


Figure 4. Temperature Coefficients

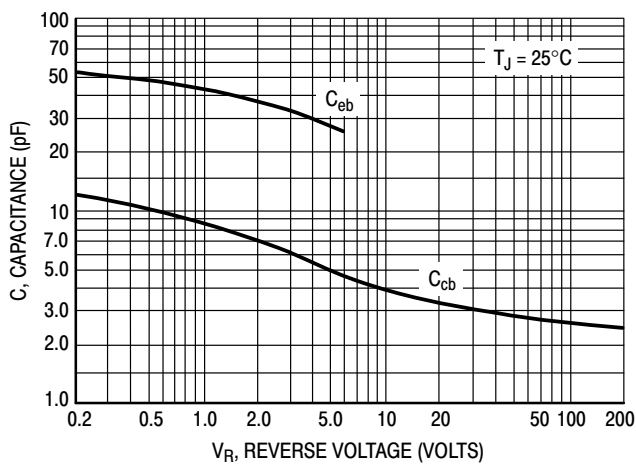


Figure 5. Capacitance

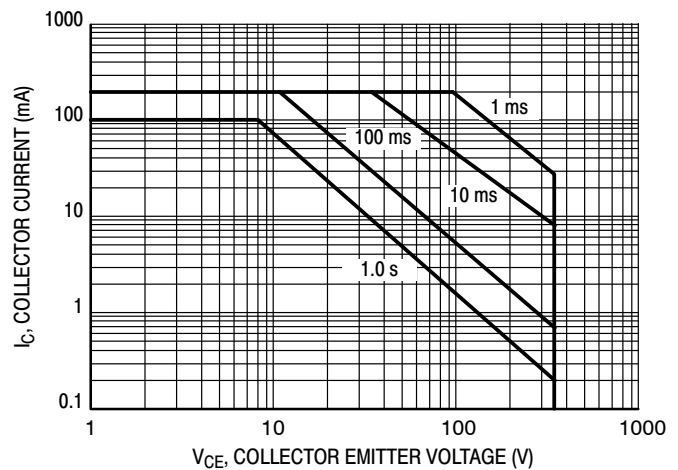


Figure 6. Safe Operating Area

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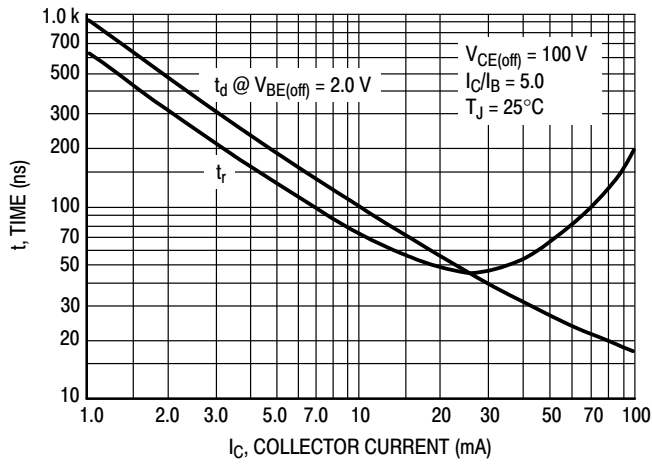


Figure 7. Turn-On Time

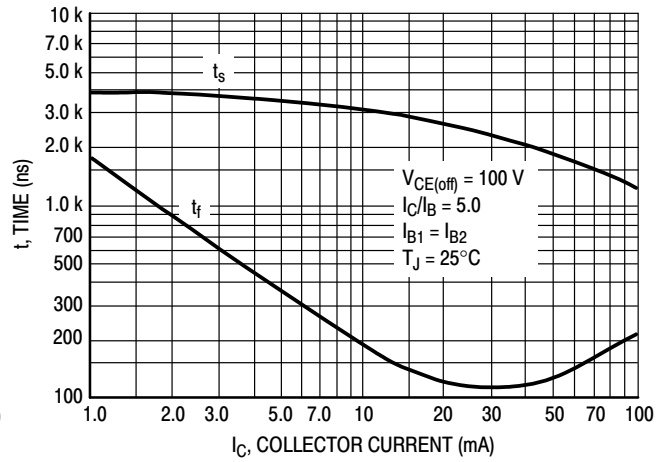


Figure 8. Turn-Off Time

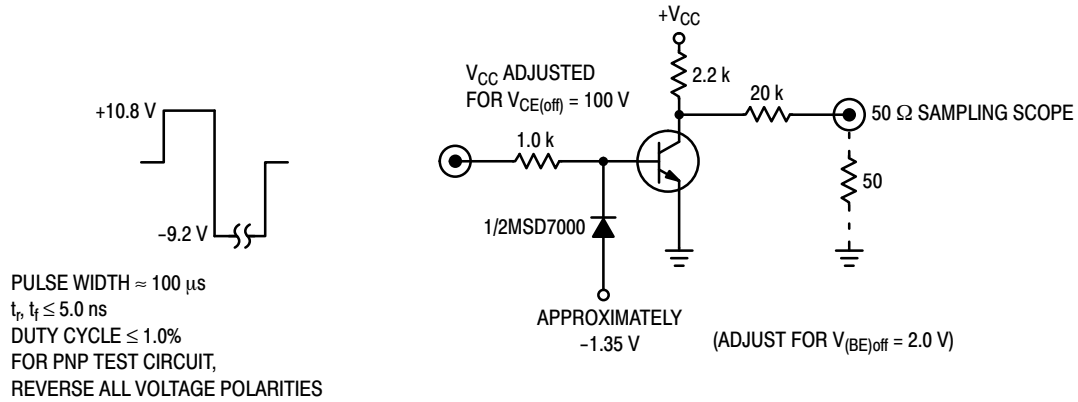


Figure 9. Switching Time Test Circuit

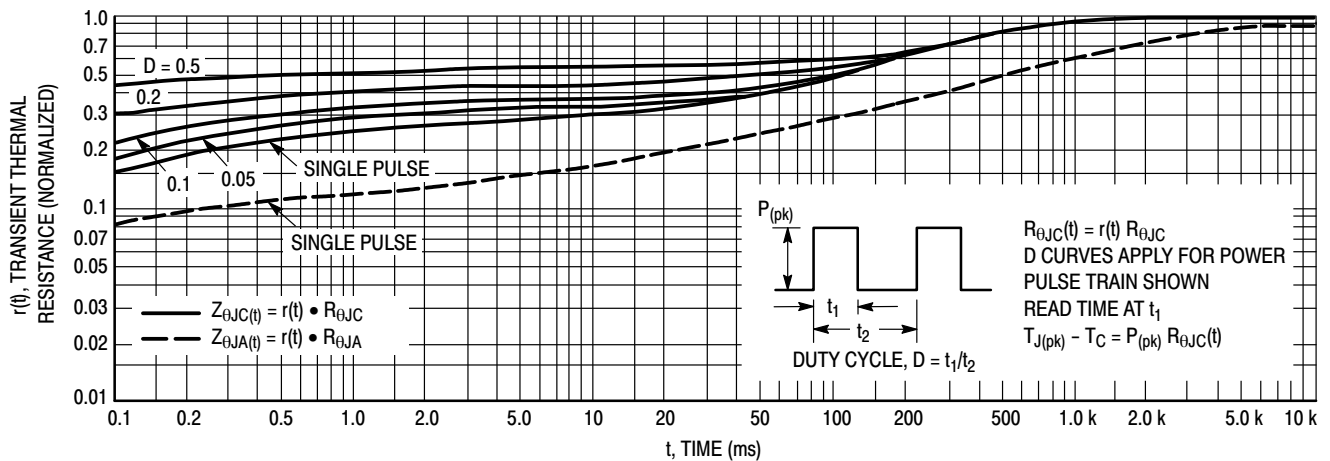


Figure 10. Thermal Response



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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